

October 1998 Revised November 2000

74LVTH125

Low Voltage Quad Buffer with 3-STATE Outputs

General Description

The LVTH125 contains four independent non-inverting buffers with 3-STATE outputs.

These buffers are designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH125 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation.

Features

- \blacksquare Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink -32 mA/+64 mA
- Functionally compatible with the 74 series 125
- Latch-up performance exceeds 500 mA
- ESD performance:

Human-body model > 2000V

Machine model > 200V

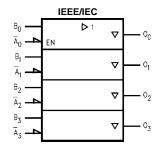
Charged-device model > 1000V

Ordering Code:

Order Number	Package Number	Package Description
74LVTH125M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
74LVTH125SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74LVTH125MTC	MTC14	114-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide

Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

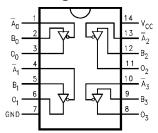
Logic Symbol



Pin Descriptions

Pin Names	Description
\overline{A}_n , B_n	Inputs
On	3-STATE Outputs

Connection Diagram



Truth Table

Inp	Output			
Ā _n	B _n	O _n		
L	L	L		
L	Н	Н		
Н	Χ	Z		

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = HIGH Impedance

Absolute Maximum Ratings(Note 1)

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	DC Output Voltage	−0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 2)	
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
Io	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA
		128	V _O > V _{CC} Output at LOW State	IIIA
I _{CC}	DC Supply Current per Supply Pin	±64		mA
I _{GND}	DC Ground Current per Ground Pin	±128		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
Тон	HIGH Level Output Current		-32	mA
I _{OL}	LOW Level Output Current		64	mA
T _A	Free-Air Operating Temperature	-40	85	°C
Δt/ΔV	Input Edge Rate, V _{IN} = 0.8V – 2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 1: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 2: Io Absolute Maximum Rating must be observed.

DC Electrical Characteristics

	Parameter		.,	T _A =	=-40°C to +8	5°C		
Symbol			V _{CC} (V)	Min	Typ (Note 3)	Max	Units	Conditions
V _{IK}	Input Clamp Diode Voltag	е	2.7			-1.2	V	I _I = -18 mA
V _{IH}	Input HIGH Voltage	Input HIGH Voltage		2.0			V	V _O ≤ 0.1V or
V _{IL}	Input LOW Voltage		2.7-3.6			0.8	V	$V_O \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7-3.6	V _{CC} - 0.2				$I_{OH} = -100 \mu A$
			2.7	2.4			V	$I_{OH} = -8 \text{ mA}$
			3.0	2.0				$I_{OH} = -32 \text{ mA}$
V _{OL}	Output LOW Voltage		2.7			0.2		$I_{OL} = 100 \mu A$
			2.7			0.5		$I_{OL} = 24 \text{ mA}$
			3.0			0.4	V	$I_{OL} = 16 \text{ mA}$
			3.0			0.5		I _{OL} = 32 mA
			3.0			0.55		$I_{OL} = 64 \text{ mA}$
I _{I(HOLD)}	Bushold Input Minimum D	rive	3.0	75			μА	V _I = 0.8V
				-75			μι	$V_1 = 2.0V$
I _{I(OD)}	Bushold Input Over-Drive		3.0	500			μА	(Note 4)
	Current to Change State			-500			μΛ	(Note 5)
I _I	Input Current		3.6			10		V _I = 5.5V
		Control Pins	3.6			±1	μА	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6			-5	μΛ	$V_I = 0V$
		Data i iiis	5.0			1		$V_I = V_{CC}$
I _{OFF}	Power Off Leakage Curre	nt	0			±100	μΑ	$0V \le V_I \text{ or } V_O \le 5.5V$
I _{PU/PD}	Power up/down 3-STATE		0-1.5V			±100	μА	V _O = 0.5V to 3.0V
	Output Current		0-1.50			±100	μΛ	$V_I = GND \text{ or } V_{CC}$
I _{OZL}	3-STATE Output Leakage	Current	3.6			-5	μΑ	$V_0 = 0.5V$
I _{OZH}	3-STATE Output Leakage	Current	3.6			5	μΑ	$V_0 = 3.0V$
I _{OZH} +	3-STATE Output Leakage	Current	3.6			10	μΑ	$V_{CC} < V_O \le 5.5V$
I _{CCH}	Power Supply Current		3.6			0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current		3.6			5	mA	Outputs LOW
I _{CCZ}	Power Supply Current		3.6			0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current		3.6			0.19	mA	$V_{CC} \le V_O \le 5.5V$
								Outputs Disabled
ΔI_{CC}	Increase in Power Supply	Current	3.6			0.2	mA	One Input at V _{CC} – 0.6V
	(Note 6)							Other Inputs at V _{CC} or GND

Note 3: All typical values are at $V_{CC} = 3.3V$, $T_A = 25$ °C.

- Note 4: An external driver must source at least the specified current to switch from LOW-to-HIGH.
- Note 5: An external driver must sink at least the specified current to switch from HIGH-to-LOW.
- Note 6: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 7)

Symbol	Parameter	v _{cc}	T _A = 25°C			Units	Conditions	
Symbol	T drameter	(V)	Min	Тур	Max	Omio	$\textbf{C}_{\textbf{L}} = \textbf{50 pF, R}_{\textbf{L}} = \textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 8)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 8)	

Note 7: Characterized in SOIC package. Guaranteed parameter, but not tested.

Note 8: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

AC Electrical Characteristics

			$T_A = -40^{\circ}\text{C to} + 85^{\circ}\text{C}$ $C_L = 50 \text{ pF}, R_L = 500\Omega$					
Symbol	Parameter		$V_{CC} = 3.3V \pm 0.3V$	V _{CC} = 2.7V		Units		
		Min	Typ (Note 9)	Max	Min	Max		
t _{PLH}	Propagation Delay Data to Output	1.0		3.5	1.0	4.5		
t _{PHL}		1.0		3.9	1.0	4.9	ns	
t _{PZH}	Output Enable Time	1.0		4.0	1.0	5.5	ns	
t _{PZL}		1.1		4.0	1.1	5.4	115	
t _{PHZ}	Output Disable Time	1.5		4.5	1.5	5.7	ns	
t_{PLZ}		1.3		4.5	1.3	4.0	115	
t _{OSHL}	Output to Output Skew (Note 10)			1.0		1.0	ns	

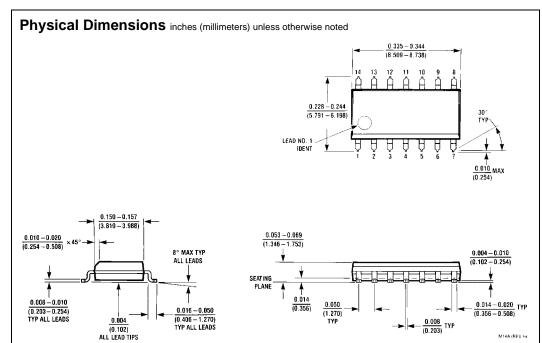
Note 9: All typical values are at $V_{CC} = 3.3V$, $T_A = 25$ °C.

Note 10: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

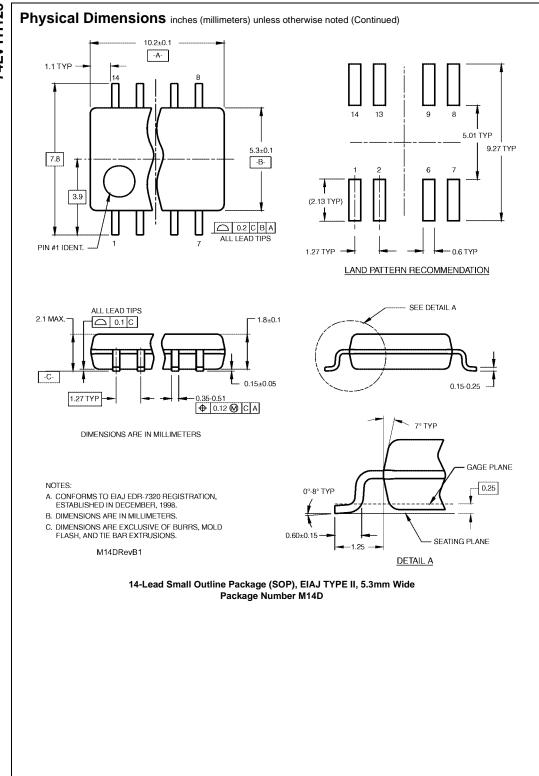
Capacitance (Note 11)

Symbol	Parameter	Conditions	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 0V$, $V_I = 0V$ or V_{CC}	4	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.0V$, $V_O = 0V$ or V_{CC}	8	pF

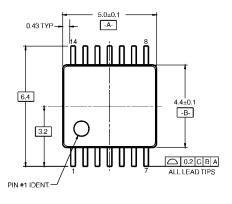
Note 11: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.

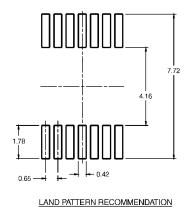


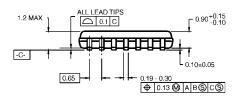
14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow Package Number M14A

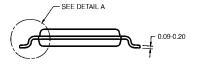


Physical Dimensions inches (millimeters) unless otherwise noted (Continued)





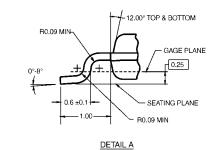




NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-153, VARIATION AB, REF NOTE 6, DATE 7/93.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M, 1982.

MTC14RevC3



14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide Package Number MTC14

Fairchild does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and Fairchild reserves the right at any time without notice to change said circuitry and specifications.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

www.fairchildsemi.com